

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	30	mA
Base Current	I_B	10	mA
Collector Power Dissipation	P_C	310	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55~150	

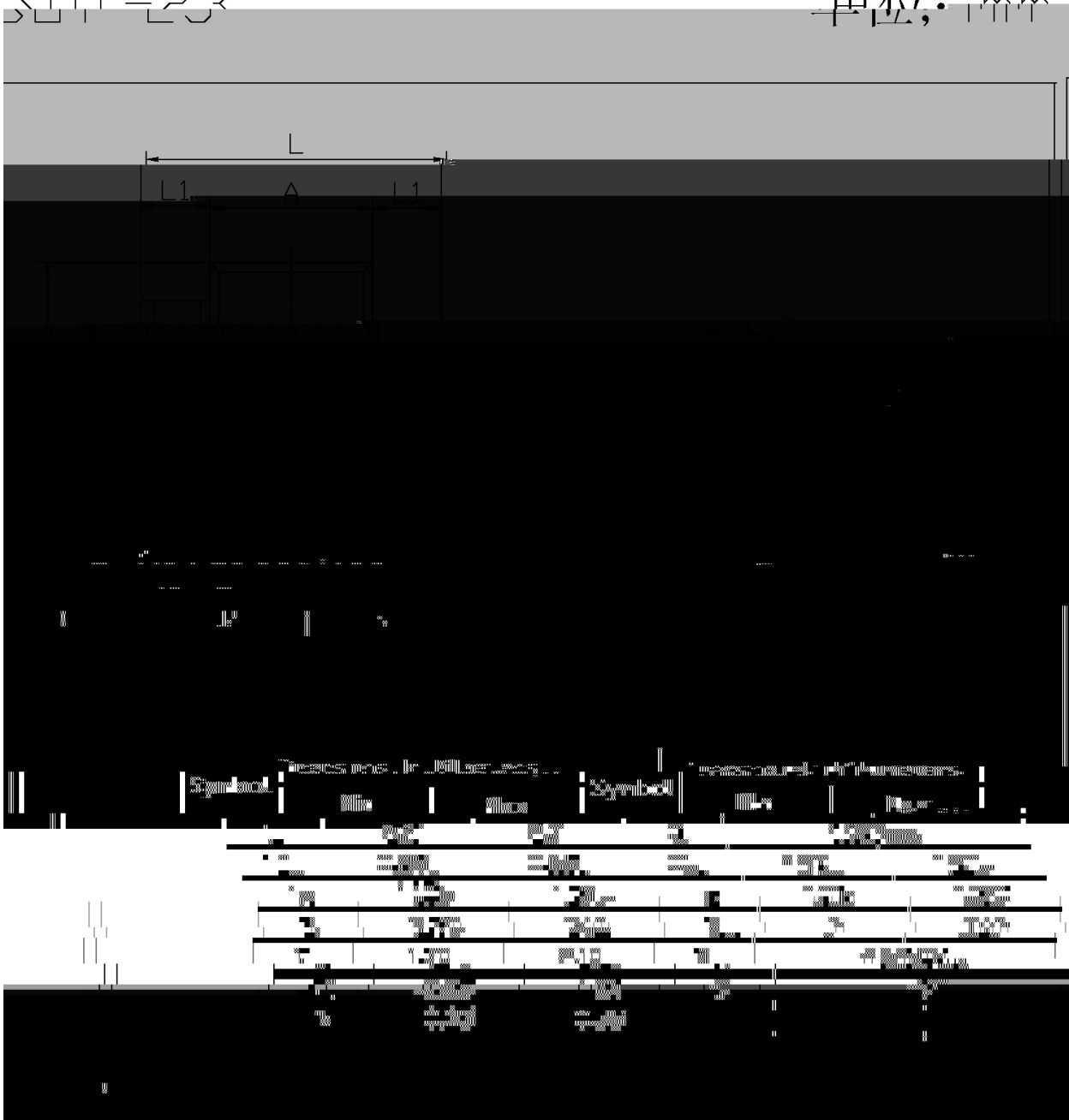
/ Electrical Characteristics(Ta=25)

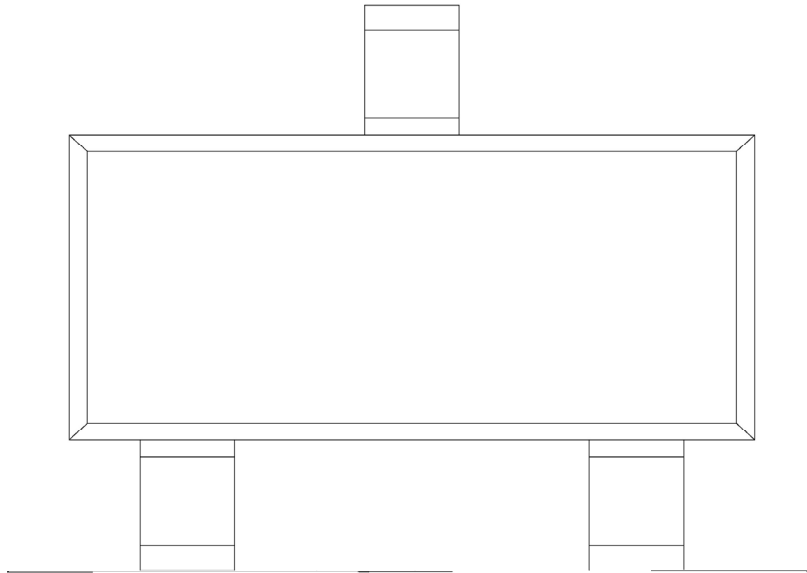
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=0.1mA$ $I_E=0$	50			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$ $I_B=0$	30			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=0.1mA$ $I_C=0$	5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=50V$ $I_E=0$			0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=5.0V$ $I_C=1.0mA$	28		198	
Collector-Emitter Saturation voltage	$V_{CE(sat)}$	$I_C=10mA$ $I_B=1.0mA$		0.08	0.3	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=5.0V$ $I_C=1.0mA$		0.7	0.75	V
Current Gain Bandwidth Product	f_T	$V_{CE}=5.0V$ $I_C=1.0mA$	150	370		MHz
Output Capacitance	C_{ob}	$V_{CB}=10V$ $I_E=0$ $f=1.0MHz$		1.5		pF
Noise Figure	NF	$V_{CE}=5.0V$ $I_C=1.0mA$ $R_g=500\Omega$ $f=1.0MHz$		2.0	4.0	dB

/ Package Dimensions

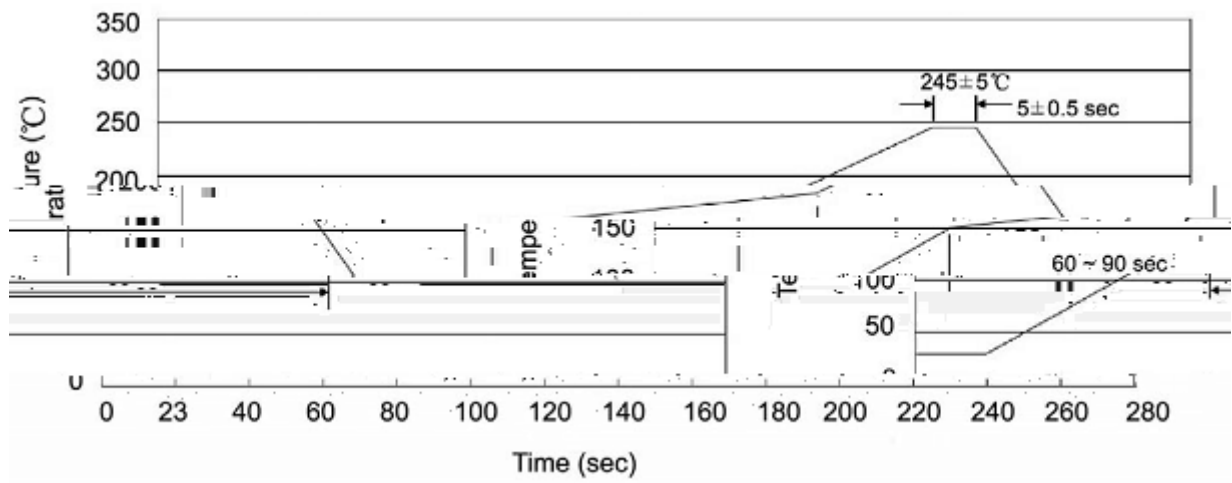
SOT-23

单位: mm





() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|----|-----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245±5 | | | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec
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/ Packaging SPEC.